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## Amendments to the Specification

*Please amend the below-number paragraphs of the original specification as follows:*

**[0050]** FIG. 3 illustrates a conventional wafer cleaning apparatus aimed at obviating the problems described above in connection with the system of FIG. 1. In this apparatus, a plurality of wafers W are separated from the cassette C and stand by, a cleaning chamber 30 is filled with a cleaning solution comprising chemicals diluted with the de-ionized water, and the wafers W are submerged in the cleaning solution. After a given time elapses, i.e., once enough time has been given for the cleaning solution to clean the wafers W, the cleaning solution is discharged from the cleaning chamber 30 while de-ionized water is supplied into the chamber 30. Thus, the wafers W are rinsed in the same chamber 30. Next, the de-ionized water is drained from the chamber 30 while the chamber 30 is filled with IPA vapor, thereby drying the wafers. Subsequently, heated N<sub>2</sub> gas is introduced into the cleaning chamber 30 while the IPA vapors are discharged.

**[0125]** In a first embodiment (case 1 of FIG. 6), the inner diameter (parameter B) of each de-ionized water supply nozzle 34 was 1.8 ~ 2.3mm, ~~each set of de-ionized water supply nozzle holes was made up of nozzle 34~~ included twelve (12) ~~individual sets of~~ nozzle holes 40, and the diameter of each of the nozzle holes was  $\sim 0.8 \pm 0.005$  mm (parameter C). Furthermore, each set of nozzles holes 40 subtended an angle (parameter D) of 90° from the axial center of the nozzle 34 such that the deionized water issuing from each set of nozzle holes 40 is sprayed in at an angle of 90° from the nozzle 34.